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(54) Title: CHALCOGENIDE-BASED PHOTOVOLTAIC DEVICES AND METHODS OF MANUFACTURING THE SAME

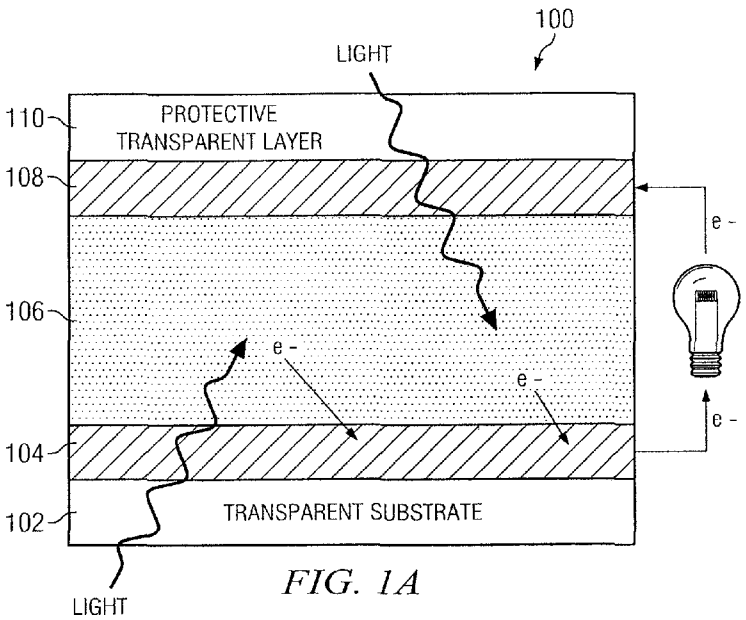


FIG. 1A

(57) Abstract: In one example embodiment, a method includes sputtering one or more absorber layers over a substrate. In a particular embodiment, the substrate is preheated to a substrate temperature of at least approximately 300 degrees Celsius prior to the sputtering and during the sputtering of each of one or more of the absorber layers, and the sputtering of at least one of the absorber layers is performed in a sputtering atmosphere having a pressure of at least 0.5 Pascals. Additionally, in a particular embodiment, the sputtering of at least one of the absorber layers comprises sputtering from a sputter target that comprises a chalcogenide alloy that comprises copper (Cu) and one or more of sulfur (S), selenium (Se), or tellurium (Te).

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